23. (Amended)   Structure according to Claim 20, charchterized in that the thin layer (2) is made integral with a support (3) through an intermediate conductive surface.

26. (Amended)   Structure according to Claim 23, characterized in that deposition of conductive bonding materials is associated with said metal interface layer.

28. (Amended)   Structure according to Claim 22, characterized in that the thin layer (2) is made integral with a support (3) through the use of a brazing material.

30. (Amended)   Structure according to any one of Claim 20, characterized in that the material of the thin layer (2) is chosen from among SiC, GaAs and InP.

31. (Amended)   Structure according to Claim 23, characterized in that the support (3) is made of silicon.

Please add claims 32-36 as follows:

32. (New)   Structure according to Claim 22, characterized in that the thin layer (2) is made integral with a support (3) through an intermediate conductive interface.

33. (New)   Structure according to Claim 25, characterized in that deposition of conductive bonding materials is associated with said metal interface layer.